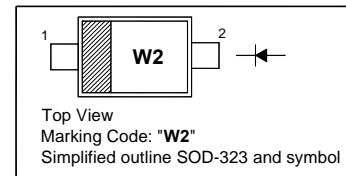


**Silicon Epitaxial Planar Switching Diode**
**PINNING**

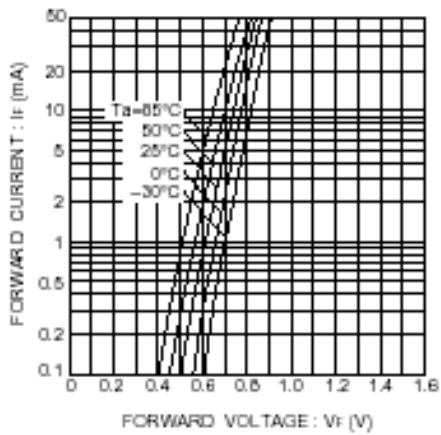
PIN	DESCRIPTION
1	Cathode
2	Anode


**Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )**

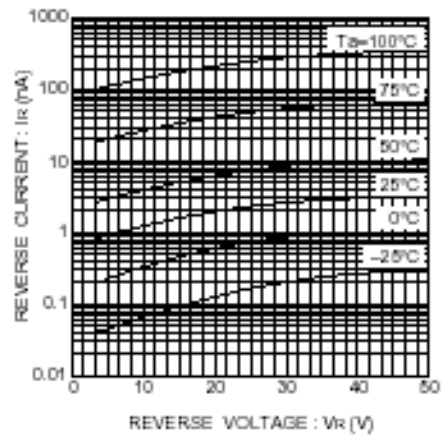
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	85	V
Reverse Voltage	$V_R$	75	V
Continuous Forward Current	$I_F$	125	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	at $t = 1\text{ s}$ 0.5	A
		at $t = 1\text{ ms}$ 1	
		at $t = 1\text{ }\mu\text{s}$ 4	
Power Dissipation	$P_{tot}$	250	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

**Characteristics at  $T_a = 25\text{ }^\circ\text{C}$** 

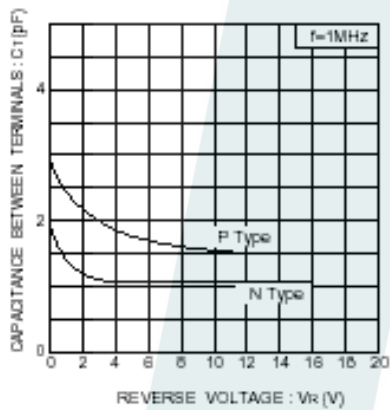
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	$V_F$	715	mV
		855	mV
		1	V
		1.25	V
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_j = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_j = 150\text{ }^\circ\text{C}$	$I_R$	30	nA
		1	$\mu\text{A}$
		30	$\mu\text{A}$
		50	$\mu\text{A}$
Diode Capacitance at $V_R = 0, f = 1\text{ MHz}$	$C_d$	2	pF
Reverse Recovery Time at $I_F = 10\text{ mA}, I_R = 10\text{ mA}, R_L = 100\text{ }\Omega$	$t_{rr}$	4	ns



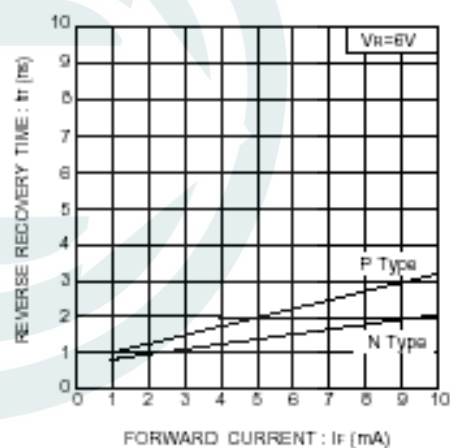
Forward characteristics



Reverse characteristics



Capacitance between terminals characteristics

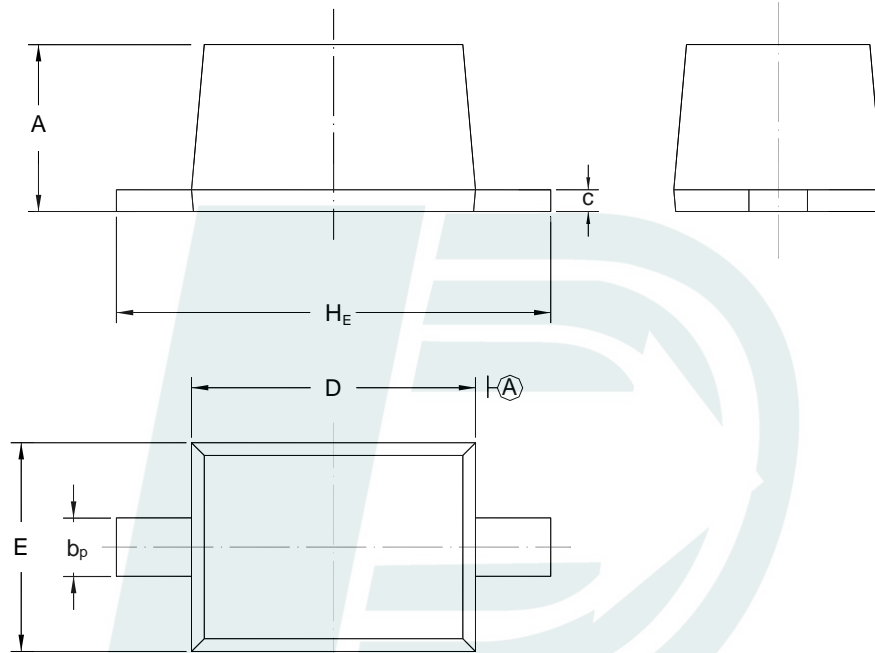


Reverse recovery time

**PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30